TOSHIBA Transistor Silicon Npn Epitaxial Type (PCT Process)

HN1C03FU

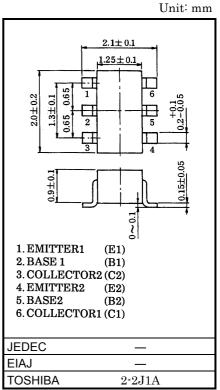
For Muting and Switching Applications

- Including two devices in US6 (ultra super mini type with 6 leads)
- High emitter-base voltage: $V_{EBO} = 25V$ (min)
- High reverse hfe: reverse hfe = 150 (typ.)(Vce =-2V, Ic =-4mA)
- Low on resistance: $R_{ON} = 1\Omega$ (typ.)($I_B = 5mA$)

Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V _{CEO}	20	٧
Emitter-base voltage	V _{EBO}	25	٧
Collector current	IC	300	mA
Base current	ΙΒ	60	mA
Collector power dissipation	P _C *	200	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C

^{*} Total rating



Weight: 6.8mg

Electrical Characteristics (Ta = 25°C) (Q1,Q2 Common)

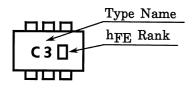
Characteristic		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cu	ut-off current	I _{CBO}	_	V _{CB} = 50V, I _E = 0	_	_	0.1	μΑ
Emitter cut-	off current	I _{EBO}	-	V _{EB} = 25V, I _C = 0	_	_	0.1	μΑ
DC current	gain	h _{FE (note)}	_	$V_{CE} = 2V$, $I_C = 4mA$	200		1200	
Collector-er voltage	mitter saturation	V _{CE (sat)}	_	I _C = 30mA, I _B = 3mA	_	0.042	0.1	V
Base-emitter voltage		V _{BE}	_	V _{CE} = 2V, I _C = 4mA	_	0.61	_	V
Transition frequency		f _T	_	V_{CE} = 6V, I_C = 4mA	_	30	_	MHz
Collector output capacitance		C _{ob}	-	V _{CB} = 10V, I _E = 0, f = 1MHz	_	4.8	7	pF
Switching time	Turn-on time	_	_	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	_	160	_	
	Storage time	_	_		_	500	_	ns
	Fall time	_	_		_	130	_	

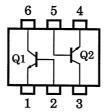
Note: hfe Classification

A: 200~700, B: 350~1200

Marking

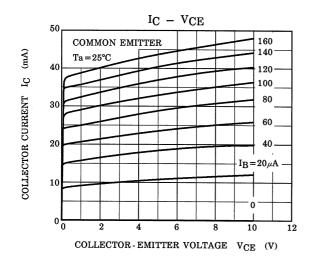
Equivalent Circuit (Top View)

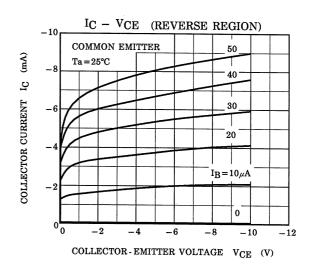


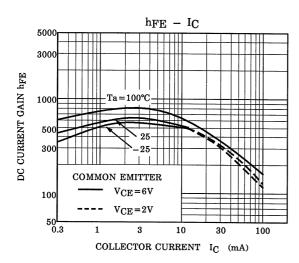


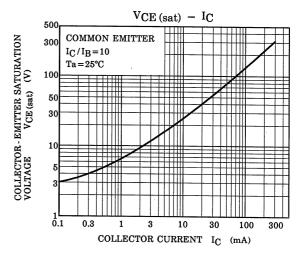
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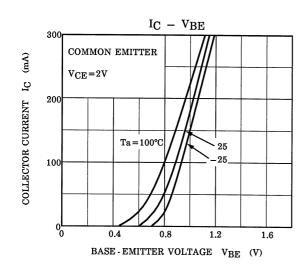
(Q1,Q2 Common)

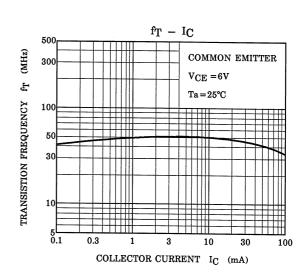






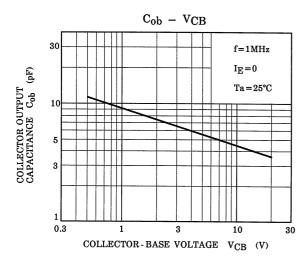


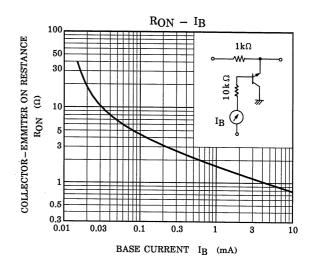


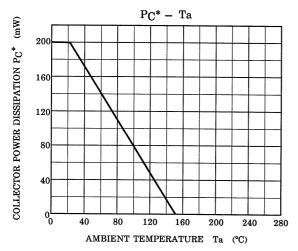


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(Q1,Q2 Common)







*: Total Rating

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